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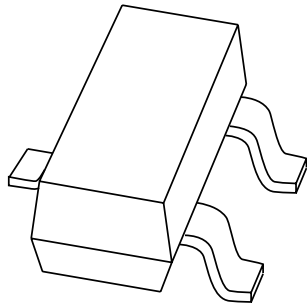
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Kind regards,

Team Nexperia

# DATA SHEET



**PBSS9110T**

100 V, 1 A

PNP low  $V_{CEsat}$  (BISS) transistor

Product data sheet  
Supersedes data of 2004 May 06

2004 May 13

**100 V, 1 A  
PNP low  $V_{CEsat}$  (BISS) transistor**

**PBSS9110T**

**FEATURES**

- SOT23 package
- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability:  $I_C$  and  $I_{CM}$
- Higher efficiency leading to less heat generation

**APPLICATIONS**

- Major application segments
  - Automotive 42 V power
  - Telecom infrastructure
  - Industrial
- DC-to-DC conversion
- Peripheral drivers
  - Driver in low supply voltage applications (e.g. lamps and LEDs).
  - Inductive load driver (e.g. relays, buzzers and motors).

**DESCRIPTION**

PNP low  $V_{CEsat}$  transistor in a SOT23 plastic package.  
NPN complement: PBSS8110T.

**MARKING**

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PBSS9110T	*U7

**Note**

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

**ORDERING INFORMATION**

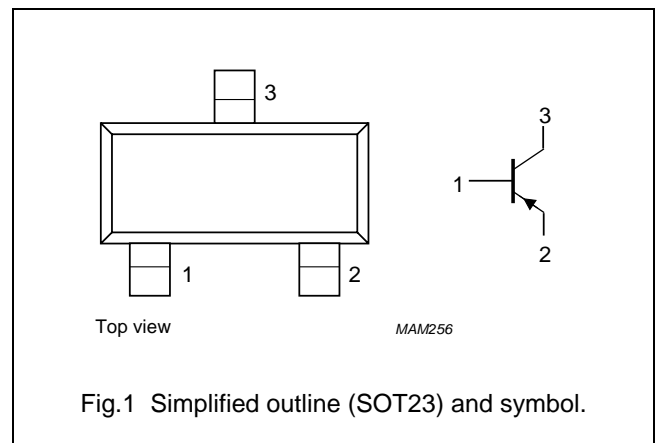
TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS9110T	–	plastic surface mounted package; 3 leads	SOT23

**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	–100	V
$I_C$	collector current (DC)	–1	A
$I_{CM}$	repetitive peak collector current	–3	A
$R_{CEsat}$	equivalent on-resistance	320	m $\Omega$

**PINNING**

PIN	DESCRIPTION
1	base
2	emitter
3	collector



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PBSS9110T

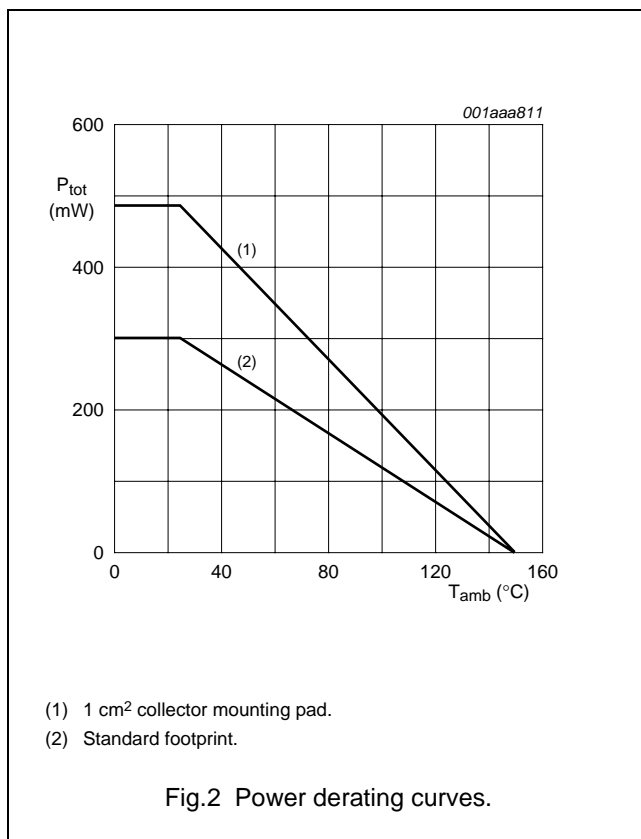
**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–120	V
$V_{CEO}$	collector-emitter voltage	open base	–	–100	V
$V_{EBO}$	emitter-base voltage	open collector	–	–5	V
$I_C$	collector current (DC)		–	–1	A
$I_{CM}$	peak collector current	limited by $T_{j(max)}$	–	–3	A
$I_B$	base current (DC)		–	–300	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$ ; note 1	–	300	mW
		$T_{amb} \leq 25\text{ }^\circ\text{C}$ ; note 2	–	480	mW
$T_j$	junction temperature		–	150	$^\circ\text{C}$
$T_{amb}$	operating ambient temperature		–65	+150	$^\circ\text{C}$
$T_{stg}$	storage temperature		–65	+150	$^\circ\text{C}$

**Notes**

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated, standard footprint.
2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and 1 cm<sup>2</sup> collector mounting pad.



100 V, 1 A  
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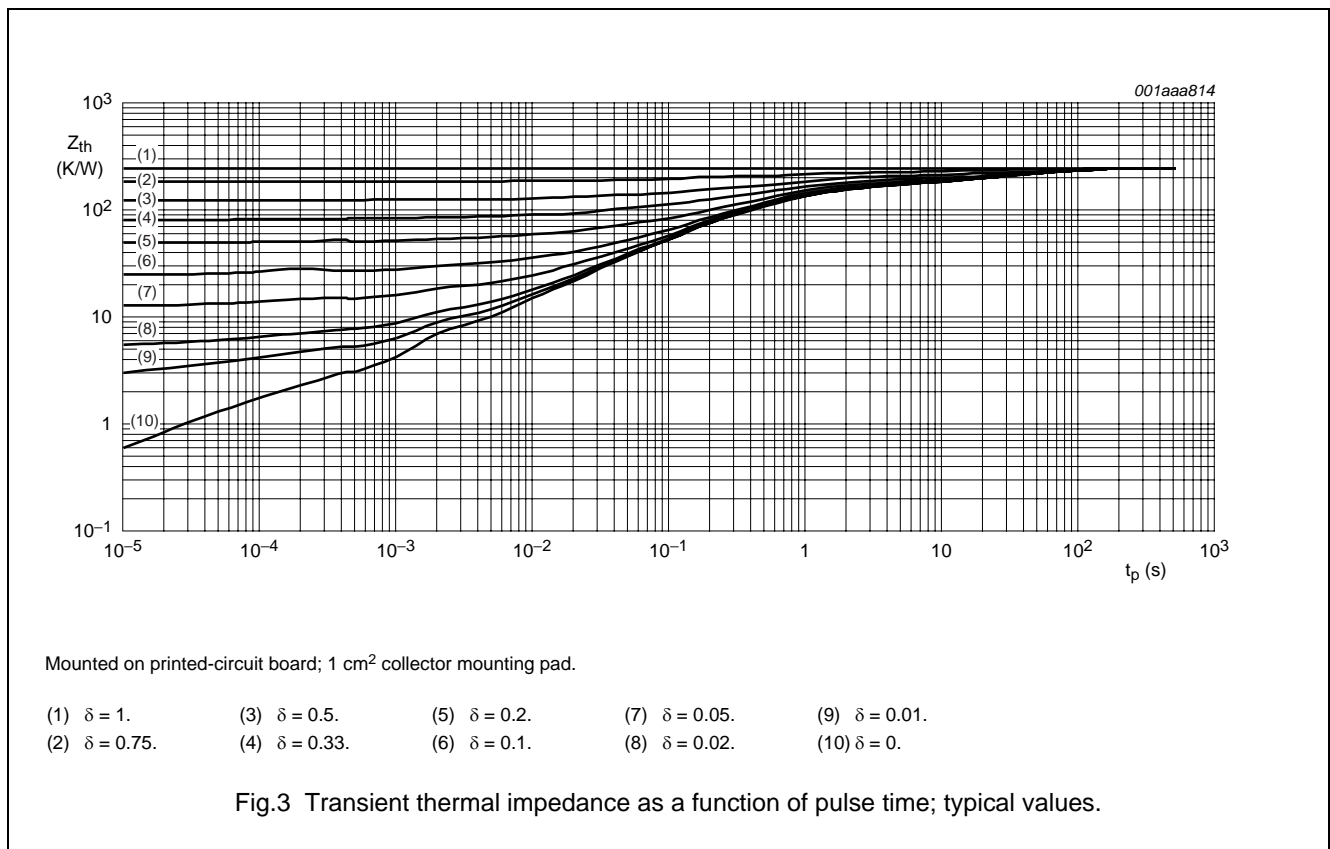
PBSS9110T

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

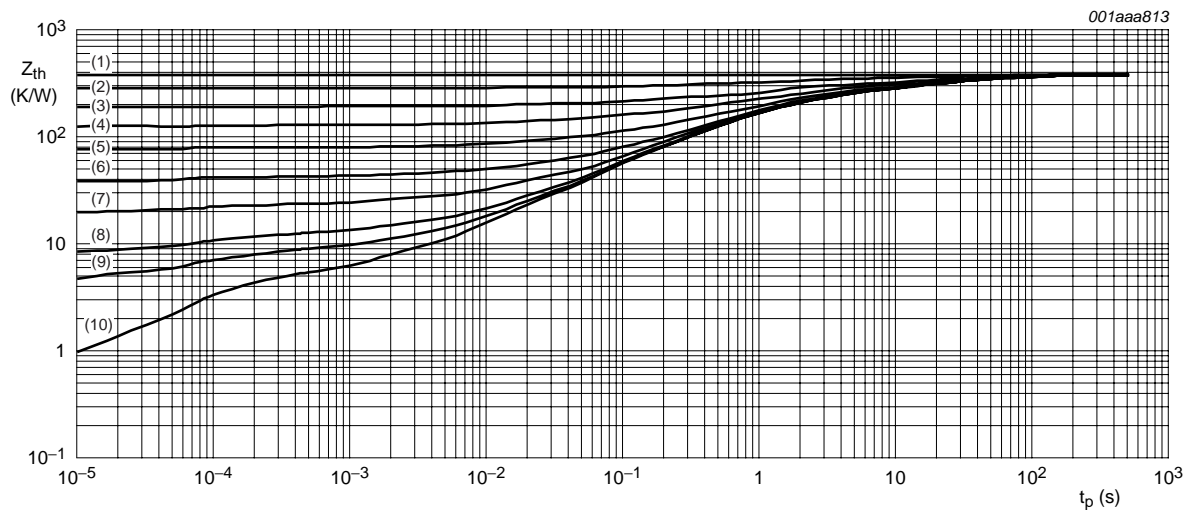
**Notes**

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2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and 1 cm<sup>2</sup> collector mounting pad.



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PBSS9110T



Mounted on printed-circuit board; standard footprint.

- |                      |                      |                     |                      |                      |
|----------------------|----------------------|---------------------|----------------------|----------------------|
| (1) $\delta = 1.$    | (3) $\delta = 0.5.$  | (5) $\delta = 0.2.$ | (7) $\delta = 0.05.$ | (9) $\delta = 0.01.$ |
| (2) $\delta = 0.75.$ | (4) $\delta = 0.33.$ | (6) $\delta = 0.1.$ | (8) $\delta = 0.02.$ | (10) $\delta = 0.$   |

Fig.4 Transient thermal impedance as a function of pulse time; typical values.

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PBSS9110T

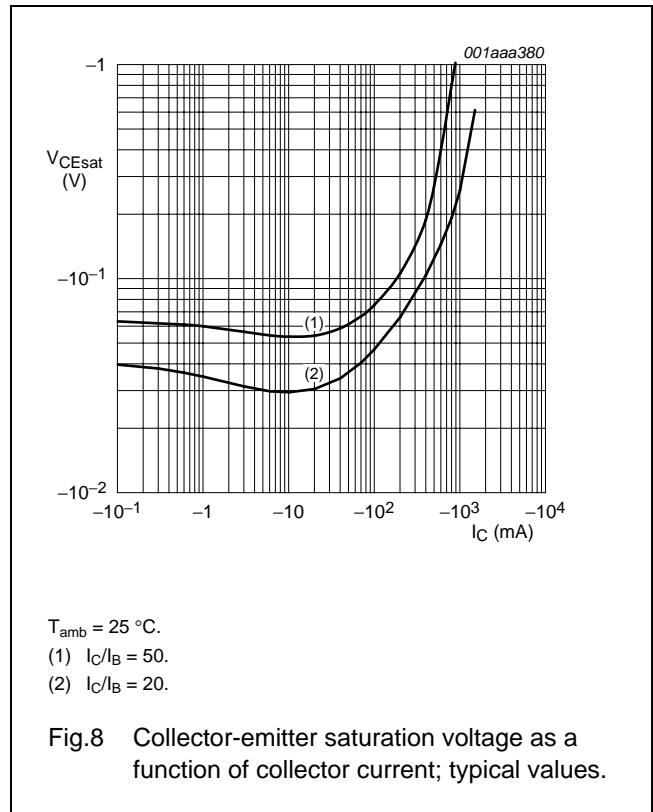
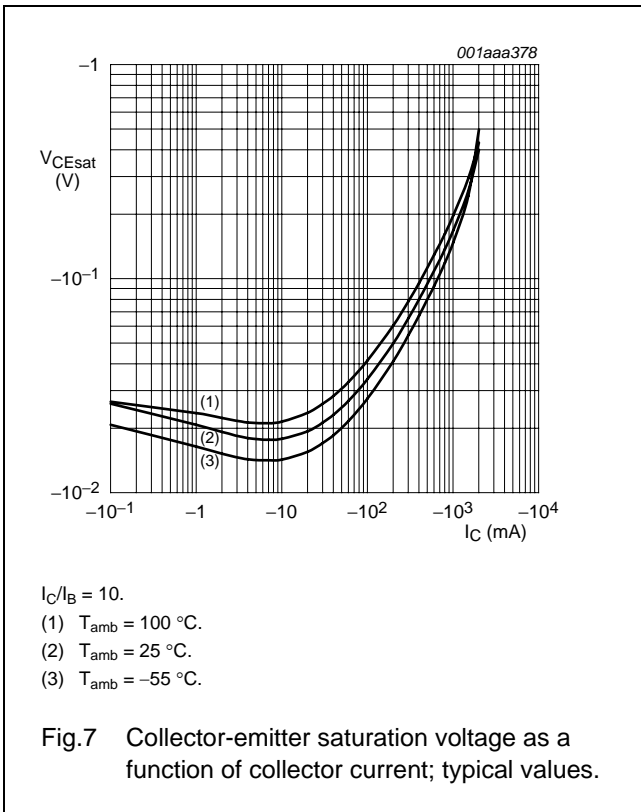
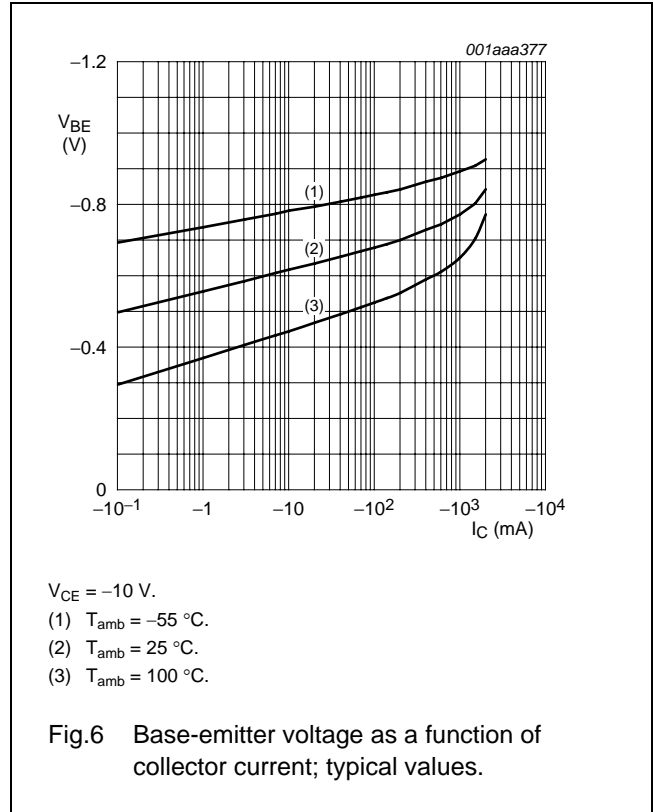
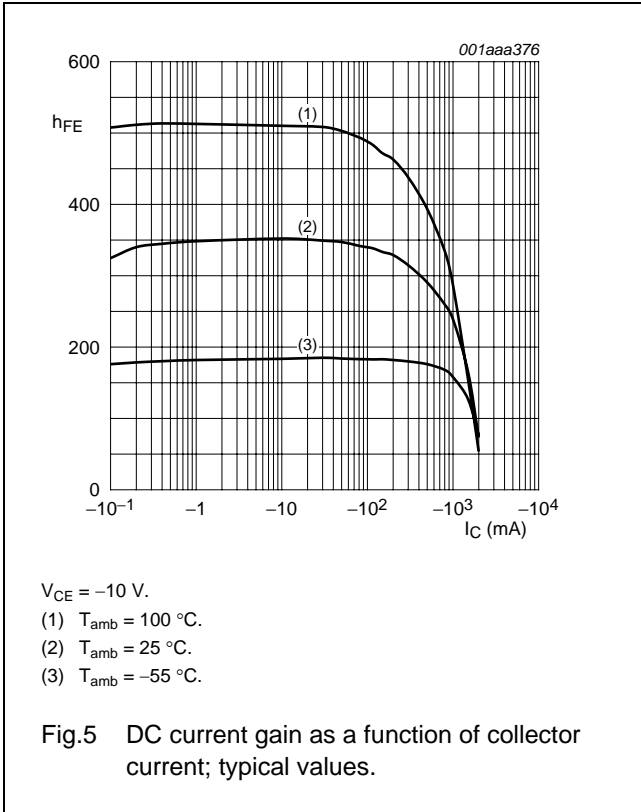
**CHARACTERISTICS** $T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -80\text{ V}; I_E = 0\text{ A}$	–	–	–100	nA
		$V_{CB} = -80\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ °C}$	–	–	–50	$\mu\text{A}$
$I_{CES}$	collector-emitter cut-off current	$V_{CE} = -80\text{ V}; V_{BE} = 0\text{ A}$	–	–	–100	nA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -4\text{ V}; I_C = 0\text{ A}$	–	–	–100	nA
$h_{FE}$	DC current gain	$V_{CE} = -5\text{ V}; I_C = -1\text{ mA}$	150	–	–	
		$V_{CE} = -5\text{ V}; I_C = -250\text{ mA}$	150	–	–	
		$V_{CE} = -5\text{ V}; I_C = -500\text{ mA}$ ; note 1	150	–	450	
		$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$ ; note 1	125	–	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -250\text{ mA}; I_B = -25\text{ mA}$	–	–	–120	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–	–180	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$ ; note 1	–	–	–320	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = -1\text{ A}; I_B = -100\text{ mA}$ ; note 1	–	170	320	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -100\text{ mA}$	–	–	–1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	–	–	–1	V
$f_T$	transition frequency	$V_{CE} = -10\text{ V}; I_C = -50\text{ mA}$ ; $f = 100\text{ MHz}$	100	–	–	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0\text{ A}$ ; $f = 1\text{ MHz}$	–	–	17	pF

**Note**1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

100 V, 1 A  
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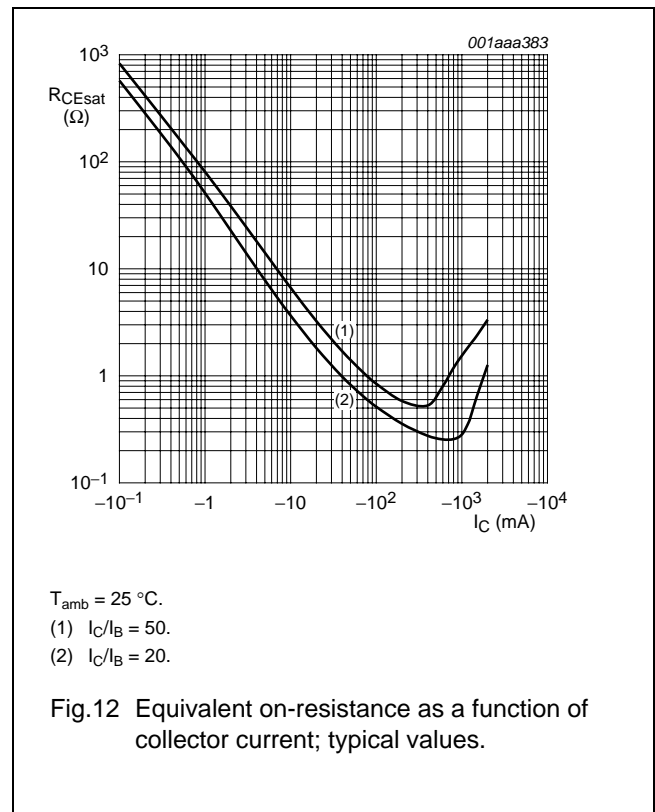
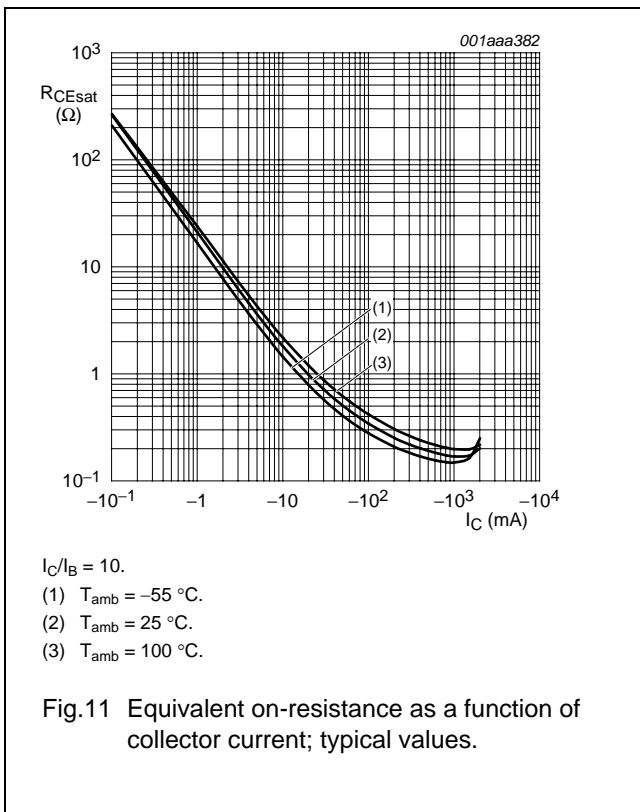
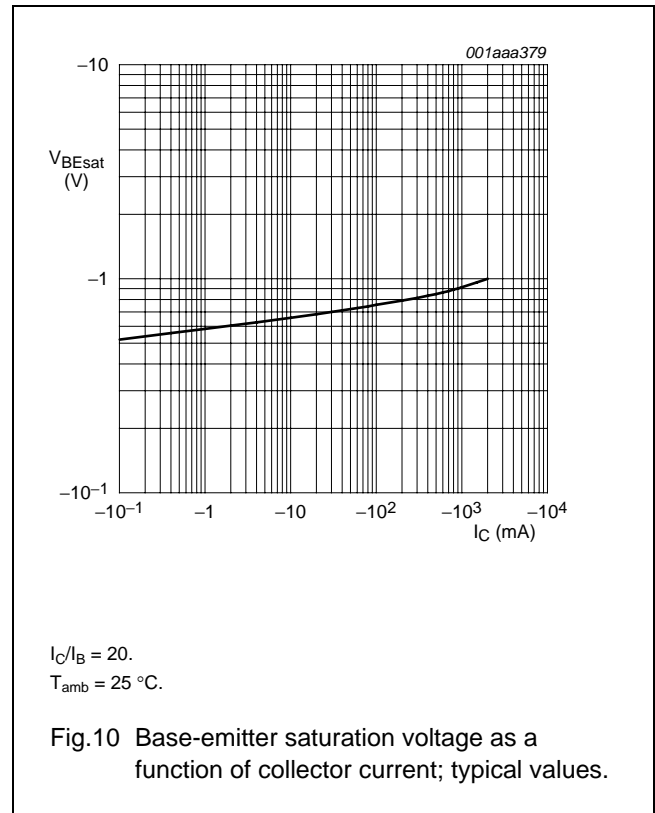
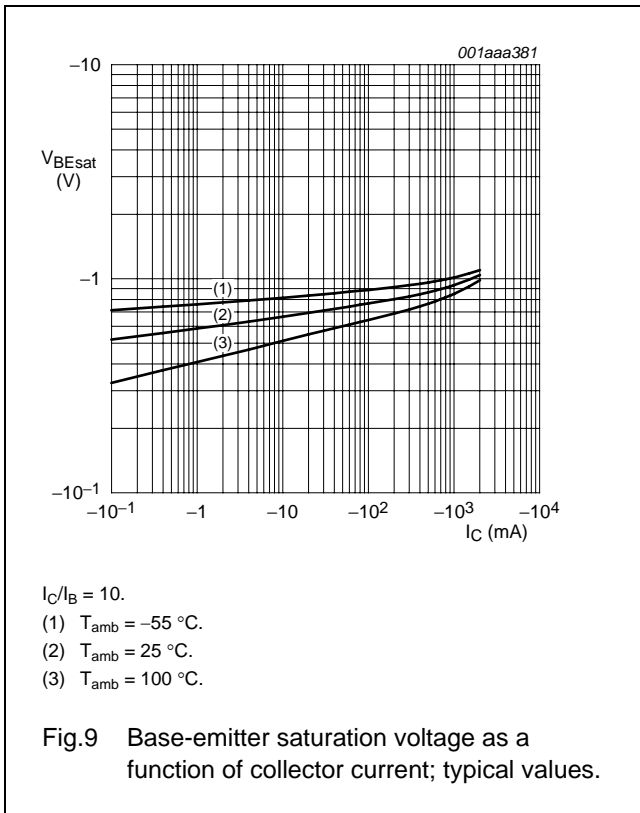
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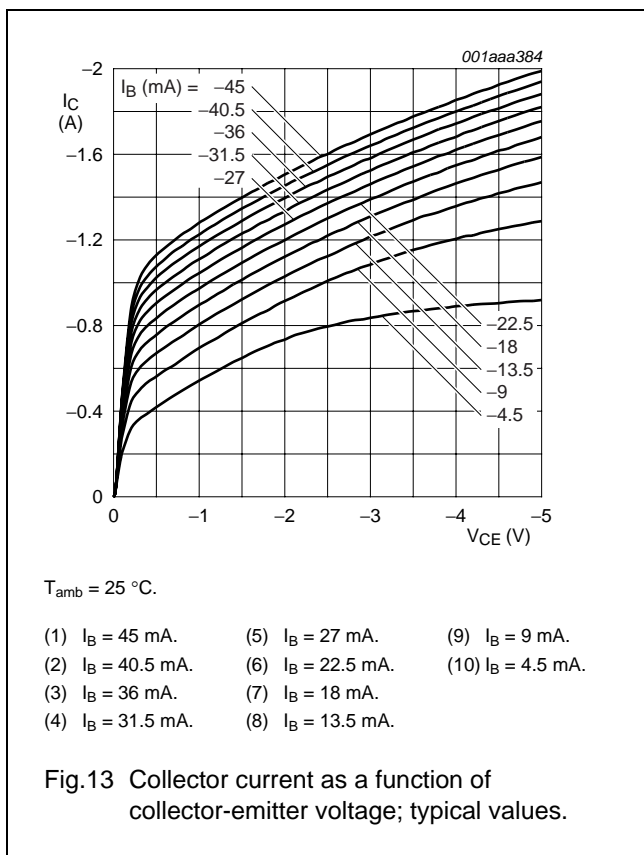
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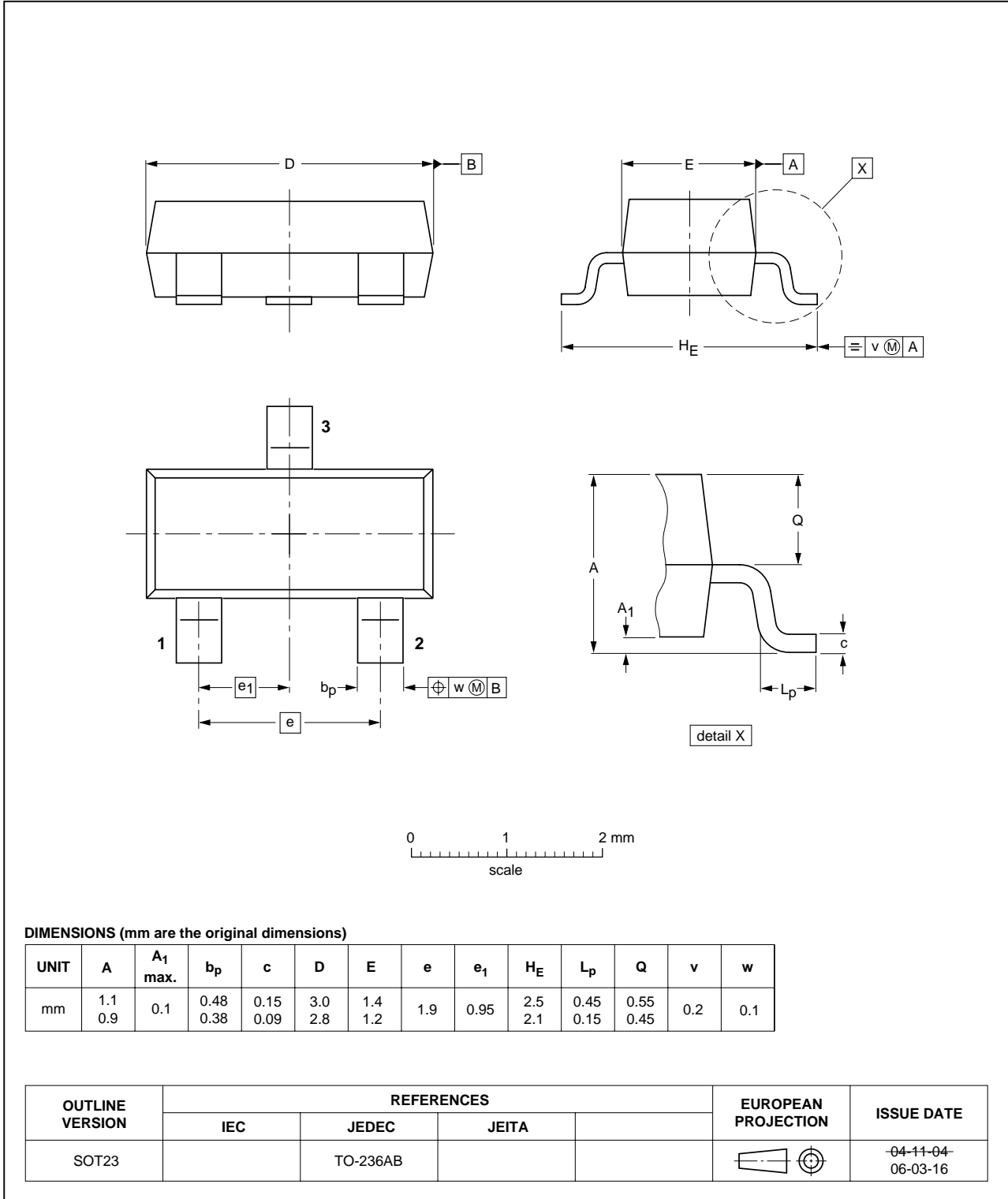
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PBSS9110T

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



100 V, 1 A  
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PBSS9110T

**DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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